

MMDL770T1

Schottky Barrier Diode

Schottky barrier diodes are designed primarily for high-efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance – 1.0 pF @ 20 V
- Low Reverse Leakage – 200 nA (max)
- High Reverse Voltage – 70 Volts (min)
- Available in 8 mm Tape and Reel
- Device Marking: 5H

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_R	Reverse Voltage	70	Vdc

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
P_D	Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$ Derate above 25°C	200	mW
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	1.57	$\text{mW}/^\circ\text{C}$
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

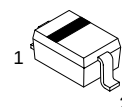
*FR-5 Minimum Pad



ON Semiconductor™

<http://onsemi.com>

1.0 pF SCHOTTKY BARRIER DIODE



PLASTIC
SOD-323
CASE 477



ORDERING INFORMATION

Device	Package	Shipping
MMDL770T1	SOD-323	3000 / Tape & Reel